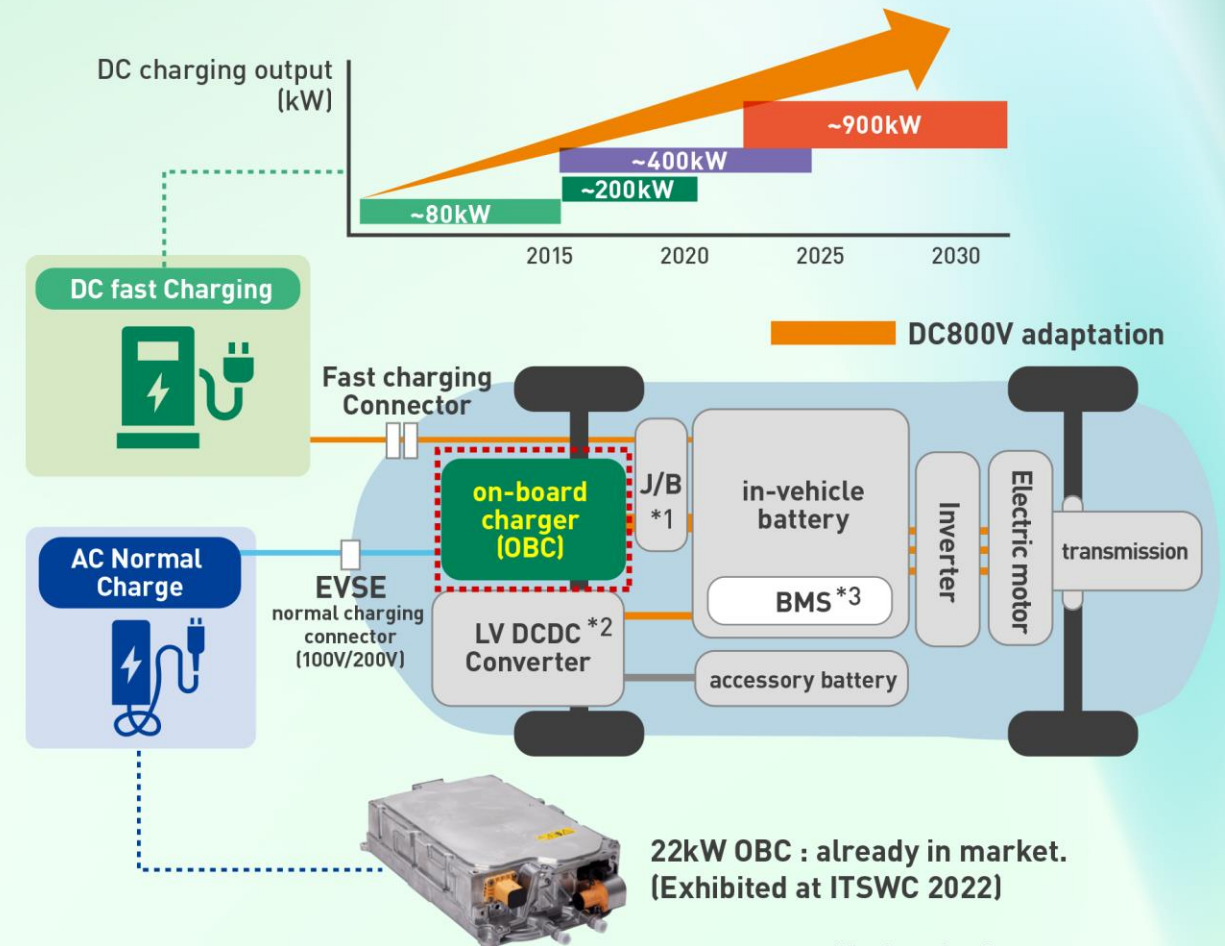


OBC (800V/22kW) Using Wide-Bandgap Semiconductors

Benefits

Customer satisfaction improvement
by 800V system and 22kW OBC
introduction.

- AC/DC Charging time reduction
- DC conduction loss reduction
- Power consumption reduction
- Weight reduction



- *1 : Junction box
- *2 : Low Voltage DCDC converter
- *3 : Battery Management System



OBC (800V/22kW) Using Wide-Bandgap Semiconductors

Technical Advantages

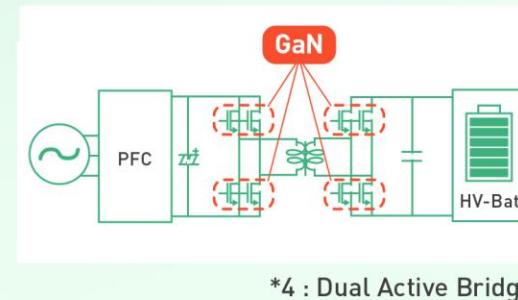
High Efficiency over wide output voltage/ current range

DAB with phase/frequency multi control algorithm by Employing Multimode Control Strategy DAB is used to extend operating time because use case is changed by bi-directional function. (V2L: x1.6 times, V2G: x10.6 times the operating time required against uni-directional OBC)

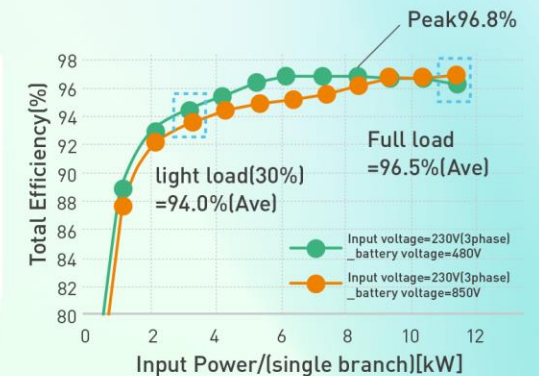
1200V GaN device

- High power/High voltage
Realize “800V/22kW” circuit technology
- High power density
2.2kW/L by 500kHz switching with GaN device
- High efficiency
96.5% by SiC→98% by Gan device (PFC+DCDC)
GaN device spec. : voltage/current : 1200V/40A
On-resistance : 15.5mΩ (target)

DAB^{*4} topology
(11kW/Branch)



Total Efficiency (SiC)



Comparison Si vs SiC vs GaN

	Si - MOSFET	SiC - MOSFET	GaN HEMT (on GaN)
Bandgap [eV]	1.1	3.3	3.4
Frequency	~1MHz	~200kHz	~1MHz
Voltage	~1kV	~several kV	~1200
Performance index [$\epsilon\mu Ec^3$]	1	440	1130



OBC (800V/22kW) Using Wide-Bandgap Semiconductors

Applications

